Yue Kuo

List of Publications by Year
in descending order

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226	2,129	249298 26	371746 37
papers	citations	h-index	g-index

230	230	230	1097
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Facing the headaches of early failures: A state-of-the-art review of burn-in decisions. Proceedings of the IEEE, 1983, 71, 1257-1266.	16.4	126
2	Reactive Ion Etching of Sputter Deposited Tantalum Oxide and Its Etch Selectivity to Tantalum. Journal of the Electrochemical Society, 1992, 139, 579-583.	1.3	60
3	Electrical and Physical Characterization of Zirconium-Doped Tantalum Oxide Thin Films. Journal of the Electrochemical Society, 2004, 151, F59.	1.3	54
4	PECVD Silicon Nitride as a Gate Dielectric for Amorphous Silicon Thin Film Transistor: Process and Device Performance. Journal of the Electrochemical Society, 1995, 142, 186-190.	1.3	53
5	Room-temperature copper etching based on a plasmaâ€"copper reaction. Applied Physics Letters, 2001, 78, 1002-1004.	1.5	51
6	Thin-Film Transistor and Ultra-Large Scale Integrated Circuit: Competition or Collaboration. Japanese Journal of Applied Physics, 2008, 47, 1845.	0.8	48
7	Hafnium-doped tantalum oxide high-k dielectrics with sub-2 nm equivalent oxide thickness. Applied Physics Letters, 2005, 87, 232906.	1.5	47
8	Electrical reliability aspects of HfO2 high-k gate dielectrics with TaN metal gate electrodes under constant voltage stress. Microelectronics Reliability, 2006, 46, 69-76.	0.9	46
9	Hafnium-Doped Tantalum Oxide High-k Gate Dielectrics. Journal of the Electrochemical Society, 2006, 153, G410.	1.3	45
10	Polycrystalline silicon formation by pulsed rapid thermal annealing of amorphous silicon. Applied Physics Letters, 1996, 69, 1092-1094.	1.5	41
11	Chlorine Plasma/Copper Reaction in a New Copper Dry Etching Process. Journal of the Electrochemical Society, 2001, 148, G524.	1.3	41
12	Zirconium-Doped Hafnium Oxide High-k Dielectrics with Subnanometer Equivalent Oxide Thickness by Reactive Sputtering. Electrochemical and Solid-State Letters, 2007, 10, H199.	2.2	40
13	Plasma Etching and Deposition for aâ€Si:H Thin Film Transistors. Journal of the Electrochemical Society, 1995, 142, 2486-2507.	1.3	39
14	Sub 2 nm Thick Zirconium Doped Hafnium Oxide High-K Gate Dielectrics. ECS Transactions, 2006, 1, 447-454.	0.3	39
15	Suppression of Crystallization of Tantalum Oxide Thin Film by Doping with Zirconium. Electrochemical and Solid-State Letters, 2005, 8, G27.	2.2	37
16	Memory functions of nanocrystalline cadmium selenide embedded ZrHfO high-kdielectric stack. Journal of Applied Physics, 2014, 115, 084113.	1.1	37
17	Plasma enhanced chemical vapor deposited silicon nitride as a gate dielectric film for amorphous silicon thin film transistorsâ€"a critical review. Vacuum, 1998, 51, 741-745.	1.6	36
18	Reactive Ion Etching of PECVD Amorphous Silicon and Silicon Nitride Thin Films with Fluorocarbon Gases. Journal of the Electrochemical Society, 1990, 137, 1235-1239.	1.3	35

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19	Etch mechanism in the low refractive index silicon nitride plasmaâ€enhanced chemical vapor deposition process. Applied Physics Letters, 1993, 63, 144-146.	1.5	35
20	A Novel Plasma-Based Copper Dry Etching Method. Japanese Journal of Applied Physics, 2000, 39, L188-L190.	0.8	33
21	Acetic Acid Extraction by Solvent Membrane. Separation Science and Technology, 1983, 18, 421-440.	1.3	32
22	Nanocrystalline ruthenium oxide embedded zirconium-doped hafnium oxide high-k nonvolatile memories. Journal of Applied Physics, 2011, 110, 024101.	1.1	31
23	A light emitting device made from thin zirconium-doped hafnium oxide high-<i>k</i> dielectric film with or without an embedded nanocrystal layer. Applied Physics Letters, 2013, 102, .	1.5	29
24	Nonvolatile hydrogenated-amorphous-silicon thin-film-transistor memory devices. Applied Physics Letters, 2006, 89, 173503.	1.5	28
25	Reactive ion etch damages in inverted, trilayer thinâ€film transistor. Applied Physics Letters, 1992, 61, 2790-2792.	1.5	27
26	Hydrogen bromide plasmaâ€"copper reaction in a new copper etching process. Thin Solid Films, 2004, 457, 326-332.	0.8	27
27	Bayesian Analysis of Hazard Rate, Change Point, and Cost-Optimal Burn-In Time for Electronic Devices. IEEE Transactions on Reliability, 2010, 59, 132-138.	3.5	27
28	Nanocrystalline Silicon Embedded Zirconium-Doped Hafnium Oxide High-kMemory Device. Japanese Journal of Applied Physics, 2006, 45, L901-L903.	0.8	24
29	Breakdown phenomena of zirconium-doped hafnium oxide high-k stack with an inserted interface layer. Applied Physics Letters, 2006, 89, 072901.	1.5	24
30	Micro light emitting device prepared from sputter deposited thin hafnium oxide film. Solid-State Electronics, 2013, 89, 120-123.	0.8	23
31	Characterization of Indium Tin Oxide and Reactive Ion Etched Indium Tin Oxide Surfaces. Japanese Journal of Applied Physics, 1990, 29, 2243-2246.	0.8	20
32	Nonvolatile Memories with Dual-Layer Nanocrystalline ZnO Embedded Zr-Doped HfO[sub 2] High-k Dielectric. Electrochemical and Solid-State Letters, 2010, 13, H83.	2.2	20
33	Light emission from conductive paths in nanocrystalline CdSe embedded Zr-doped HfO2 high-<i>k</i> stack. Applied Physics Letters, 2015, 106, .	1.5	20
34	Use of Adsorbents for Recovery of Acetic Acid from Aqueous Solutions Part Iâ€"Factors Governing Capacity. Separation and Purification Reviews, 1987, 16, 31-64.	0.8	19
35	A Selfâ€aligned, Trilayer, aâ€Si:H Thin Film Transistor Prepared from Two Photomasks. Journal of the Electrochemical Society, 1992, 139, 1199-1204.	1.3	19
36	Thin Film Transistors with Graded SiN x Gate Dielectrics. Journal of the Electrochemical Society, 1994, 141, 1061-1065.	1.3	18

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37	A new, room-temperature, high-rate plasma-based copper etch process. Vacuum, 2004, 74, 473-477.	1.6	18
38	Reactive ion etching of plasma enhanced chemical vapor deposition amorphous silicon and silicon nitride: Feeding gas effects. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 1702-1705.	0.9	17
39	Reactive Ion Etching of Sputter Deposited Tantalum with CF4, CF3Cl, and CHF3. Japanese Journal of Applied Physics, 1993, 32, 179-185.	0.8	17
40	Tantalum Nitride Interface Layer Influence on Dielectric Properties of Hafnium Doped Tantalum Oxide High Dielectric Constant Thin Films. Japanese Journal of Applied Physics, 2003, 42, L769-L771.	0.8	17
41	Physical and electrical properties of Taâ€“N, Moâ€“N, and Wâ€“N electrodes on HfO[sub 2] high-k gate dielectric. Journal of Vacuum Science & Technology B, 2006, 24, 349.	1.3	17
42	Mixed Oxide High-k Gate Dielectrics - Interface Layer Structure, Breakdown Mechanism, and Memories. ECS Transactions, 2006, 3, 253-263.	0.3	17
43	Nonvolatile memory devices with AlOx embedded Zr-doped HfO2 high-k gate dielectric stack. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 03D116.	0.6	17
44	Factors Affecting the Molybdenum Line Slope by Reactive Ion Etching. Journal of the Electrochemical Society, 1990, 137, 1907-1911.	1.3	16
45	Plasma-enhanced chemical vapor deposition of silicon nitride below 250Â°C. Vacuum, 2002, 66, 299-303.	1.6	16
46	A New Hydrogen Chloride Plasma-Based Copper Etching Process. Japanese Journal of Applied Physics, 2002, 41, 7345-7352.	0.8	15
47	Zirconium-Doped Tantalum Oxide Gate Dielectric Films Integrated with Molybdenum, Molybdenum Nitride, and Tungsten Nitride Gate Electrodes. Journal of the Electrochemical Society, 2005, 152, G643.	1.3	15
48	Charge trapping and dielectric relaxation in connection with breakdown of high-k gate dielectric stacks. Applied Physics Letters, 2006, 88, 202904.	1.5	15
49	Temperature Effects on Nanocrystalline Molybdenum Oxide Embedded ZrHfO High-<i>k</i>Nonvolatile Memory Functions. ECS Journal of Solid State Science and Technology, 2013, 2, Q16-Q22.	0.9	15
50	Factors Affecting Light Emission from Solid State Incandescent Light Emitting Devices with Sputter Deposited Zr-Doped HfO₂Thin Films. ECS Journal of Solid State Science and Technology, 2014, 3, Q182-Q189.	0.9	15
51	Nanocrystalline Zinc-Oxide-Embedded Zirconium-Doped Hafnium Oxide for Nonvolatile Memories. Journal of the Electrochemical Society, 2008, 155, H386.	1.3	14
52	Memory Functions of Nanocrystalline Indium Tin Oxide Embedded Zirconium-Doped Hafnium Oxide MOS Capacitors. Journal of the Electrochemical Society, 2007, 154, H887.	1.3	13
53	Ruthenium Modified Zr-Doped HfO2 High-k Thin Films with Low Equivalent Oxide Thickness. Journal of the Electrochemical Society, 2011, 158, G162.	1.3	13
54	Slope control of molybdenum lines etched with reactive ion etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 1529-1532.	0.9	12

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55	A New Process Using Two Photoâ€Masks to Prepare Trilayer Thin Film Transistors. Journal of the Electrochemical Society, 1991, 138, 637-638.	1.3	12
56	Doping gas effects on plasma enhanced chemical vapor deposition on heavily phosphorus-doped n+silicon film. Applied Physics Letters, 1997, 71, 2821-2823.	1.5	12
57	Single- and Dual-Layer Nanocrystalline Indium Tin Oxide Embedded ZrHfO High-k Films for Nonvolatile Memories â€“ Material and Electrical Properties. Journal of the Electrochemical Society, 2011, 158, H756.	1.3	12
58	Bayesian Analysis for Accelerated Life Tests Using a Dirichlet Process Weibull Mixture Model. IEEE Transactions on Reliability, 2014, 63, 58-67.	3.5	12
59	Thinâ€film transistors with multistep deposited amorphous silicon layers. Applied Physics Letters, 1995, 67, 2173-2175.	1.5	11
60	Additive-Gas Effects on Cl[sub 2] Plasma-Based Copper-Etch Process and Sidewall Attack. Journal of the Electrochemical Society, 2008, 155, H97.	1.3	11
61	Charge detrapping and dielectric breakdown of nanocrystalline zinc oxide embedded zirconium-doped hafnium oxide high-k dielectrics for nonvolatile memories. Applied Physics Letters, 2010, 96, 192106.	1.5	11
62	White light emission from ultrathin tungsten metal oxide film. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	11
63	Mechanism of <i>a</i>-IGZO TFT device deteriorationâ€"illumination light wavelength and substrate temperature effects. Journal Physics D: Applied Physics, 2017, 50, 42LT02.	1.3	11
64	Thin Film Technologies In Active Matrix Addressing System Of LCDs. Proceedings of SPIE, 1989, , .	0.8	10
65	Reactive ion etching of indium tin oxide by SiCl4-based plasmasâ€"substrate temperature effect. Vacuum, 1998, 51, 777-779.	1.6	10
66	Temperature Influence on Nanocrystals Embedded High-k Nonvolatile Câ€“V Characteristics. Electrochemical and Solid-State Letters, 2011, 14, H50.	2.2	10
67	Improvement of zirconium-doped hafnium oxide high-<i>k</i> dielectric properties by adding molybdenum. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	0.6	10
68	Large Area Plasma Enhanced Chemical Vapor Deposition of Nonstoichiometric Silicon Nitride. Materials Research Society Symposia Proceedings, 1992, 282, 623.	0.1	9
69	Dielectric Breakdown and Charge Trapping of Ultrathin ZrHfO/SiON High-kGate Stacks. Japanese Journal of Applied Physics, 2008, 47, 1639-1641.	0.8	9
70	Charge Trapping and Detrapping in nc-RuO Embedded ZrHfO High-k Thin Film for Nonvolatile Memory Applications. Journal of the Electrochemical Society, 2012, 159, H214-H219.	1.3	9
71	Some issues on hydrogen and hydrogenation of plasma enhanced chemical vapor deposited films in a-Si:H thin-film transistors. Vacuum, 2000, 59, 484-491.	1.6	8
72	Effects of the TaNx interface layer on doped tantalum oxide high-k films. Vacuum, 2004, 74, 539-547.	1.6	8

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73	Electromigration of Flat and Bent Copper Lines Patterned with a Plasma-Based Etch Process. Journal of the Electrochemical Society, 2009, 156, H579.	1.3	8
74	Influence of a 5â€‚ÅŠ Tantalum Nitride Interface Layer on Dielectric Properties of Zirconium-Doped Tantalum Oxide High-k Films. Journal of the Electrochemical Society, 2005, 152, G617.	1.3	7
75	Reactive Ion Etching of Titanium Tungsten Thin Films. Journal of the Electrochemical Society, 2007, 154, H653.	1.3	7
76	Grain-Size Effect on a Plasma-Based Copper Etch Process. Journal of the Electrochemical Society, 2008, 155, H432.	1.3	7
77	Temperature Effect on Dielectric Breakdown and Charges Retention of Nanocrystalline Cadmium Selenide Embedded Zr-Doped HfO2 High- ${k}$ Dielectric Thin Film. IEEE Transactions on Device and Materials Reliability, 2016, 16, 561-569.	1.5	7
78	Thin-Film Transistors. , 2003, , 723-733.		7
79	Use of Adsorbents for Recovery of Acetic Acid from Aqueous Solutions Part IIâ€"Factors Governing Selectivity. Separation and Purification Reviews, 1987, 16, 65-89.	0.8	6
80	Use of Adsorbents for Recovery of Acetic Acid from Aqueous Solutions Part IIIâ€"Solvent Regeneration. Separation and Purification Reviews, 1987, 16, 91-102.	0.8	6
81	Horizontally Redundant, Splitâ€Gate aâ€Si:H Thin Film Transistors. Journal of the Electrochemical Society, 1996, 143, 2680-2682.	1.3	6
82	Nonphotosensitive, Vertically Redundant Twoâ€Channel aâ€Si:H Thin Film Transistor. Journal of the Electrochemical Society, 1996, 143, 1469-1471.	1.3	6
83	Microchannel Electrophoresis Device for Separation and In Situ Detection of Proteins. Electrochemical and Solid-State Letters, 2001, 4, H23.	2.2	6
84	Embedding of Nanocrystalline Ruthenium in ZrHfO High-k Film for Nonvolatile Memories. ECS Transactions, 2008, 13, 465-470.	0.3	6
85	Surface Modification of Gel-Free Microchannel Surface Electrophoresis Device for DNA Identification. Japanese Journal of Applied Physics, 2008, 47, 2300-2305.	0.8	6
86	Charge Trapping Sites in nc-RuO Embedded ZrHfO High-k Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2010, 1250, 1.	0.1	6
87	Status Review of Nanocrystals Embedded High-K Nonvolatile Memories. ECS Transactions, 2011, 35, 13-31.	0.3	6
88	Non-parametric Bayesian modeling of hazard rate with a change point for nanoelectronic devices. IIE Transactions, 2012, 44, 496-506.	2.1	6
89	Memory Functions of Molybdenum Oxide Nanodots-Embedded ZrHfO High-k. Electrochemical and Solid-State Letters, 2012, 15, H192.	2.2	6
90	Temperature Effects on Charge Storage and Transfer of Nanocrystalline CdSe Embedded Zr-Doped HfO2MOS Memory Device. ECS Journal of Solid State Science and Technology, 2016, 5, Q231-Q238.	0.9	6

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91	Communicationâ€"Filtration of Light Emitted from Solid State Incandescent Light Emitting Devices. ECS Journal of Solid State Science and Technology, 2017, 6, Q39-Q41.	0.9	6
92	Numerical Analysis of Oxygen-Related Defects in Amorphous In-W-O Nanosheet Thin-Film Transistor. Nanomaterials, 2021, 11, 3070.	1.9	6
93	Singleâ€gate multichannel amorphous silicon thinâ€film transistors. Applied Physics Letters, 1995, 67, 3174-3176.	1.5	5
94	Nonvolatile Memories Based on Nanocrystalline Zinc Oxide Embedded Zirconium-doped Hafnium Oxide Thin Films. ECS Transactions, 2007, 11, 509-518.	0.3	5
95	Amorphous Silicon Based TFT and MIS Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2007, 989, 3.	0.1	5
96	Influence of pin Amorphous Silicon Stack Deposition Sequence on Solar Cell Performance and Degradation. ECS Journal of Solid State Science and Technology, 2017, 6, Q29-Q33.	0.9	5
97	Failure Mechanism of Nano-Resistor Devices. ECS Transactions, 2017, 77, 79-83.	0.3	5
98	Electromigration of Plasma Etched Copper Lines of Various Widths and Lengths. ECS Transactions, 2018, 86, 41-47.	0.3	5
99	The Role of Oxygen In the CF2Cl2 Reactive Ion Etching of Pecvd Films. Materials Research Society Symposia Proceedings, 1991, 223, 249.	0.1	5
100	Factors Affecting Reactive Ion Etching Of Corning 7059 Glass. , 1989, 1037, 103.		4
101	<title>New thin-film transistor structure and its processing method for liquid-crystal displays</title>. , 1991, 1456, 288.		4
102	Plasma Swelling of Photoresist. Japanese Journal of Applied Physics, 1993, 32, L126-L128.	0.8	4
103	High Temperature Reactive Ion Etching of Indiumâ€Tin Oxide. Journal of the Electrochemical Society, 1997, 144, 1411-1416.	1.3	4
104	Integration of an Amorphous Silicon Thin Film Transistor with a Microchannel Electrophoresis for Protein Identification. Electrochemical and Solid-State Letters, 2006, 9, J21.	2.2	4
105	Failure Analysis of Single and Dual nc-ITO Embedded ZrHfO High-k Nonvolatile Memories. ECS Transactions, 2009, 25, 457-464.	0.3	4
106	Light Effects on Charge Trapping and Detrapping of nc-ZnO Embedded ZrHfO High-k MOS Nonvolatile Memories. ECS Transactions, 2011, 41, 93-100.	0.3	4
107	Material and Electrical Properties of Hole-Trapping Memory Capacitors Composed of nc-ITO Embedded ZrHfO High-k Films. ECS Transactions, 2011, 35, 249-255.	0.3	4
108	Nonvolatile Memory Characteristics of Nanocrystalline Molybdenum Oxide Embedded High-k Film - Device Performance and Light Wavelength Effects. Materials Research Society Symposia Proceedings, 2012, 1430, 82.	0.1	4

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109	Electrical properties of nano-resistors made from the Zr-doped HfO₂high-<i>k</i>dielectric film. Journal Physics D: Applied Physics, 2018, 51, 09LT02.	1.3	4
110	Capping Layer Effect on Lifetime of Plasma Etched Copper Lines. ECS Transactions, 2019, 89, 87-92.	0.3	4
111	Lifetime of Plasma Etched Copper Lines. ECS Transactions, 2019, 90, 65-72.	0.3	4
112	Line Width and Capping Layer Effects on Electromigration Failure of Plasma Etched Copper Lines. ECS Transactions, 2019, 92, 9-16.	0.3	4
113	a-Si:H TFT Structures. , 2004, , 183-202.		4
114	Deposition of Dielectric Thin Films for a-Si:H TFT. , 2004, , 241-271.		4
115	Thin Film Transistors with Layered a-Si:H Structure. Materials Research Society Symposia Proceedings, 1995, 377, 701.	0.1	3
116	Memory Functions of Amorphous Silicon-Based Floating Gate MIS Capacitors. Electrochemical and Solid-State Letters, 2007, 10, H232.	2.2	3
117	Reliability of nc-ZnO Embedded ZrHfO High-kNonvolatile Memory Devices Stressed at High Temperatures. Materials Research Society Symposia Proceedings, 2009, 1160, 1.	0.1	3
118	Poly-Si Thin Film Formation Using a Novel Low Thermal Budget Process. Materials Research Society Symposia Proceedings, 2011, 1321, 167.	0.1	3
119	Temperature Effects on Charge Transfer Mechanisms of nc-ITO Embedded ZrHfO High-<i>k</i> Nonvolatile Memory Devices. Materials Research Society Symposia Proceedings, 2011, 1337, 123.	0.1	3
120	Electromigration study of copper lines on steps prepared by a plasma-based etch process. Journal of Applied Physics, 2012, 111, 064909.	1.1	3
121	Solid State Incandescent Light Emitting Device Made of WOx Embedded Zr-Doped HfO2 High-k Stack on Si. ECS Transactions, 2015, 66, 223-228.	0.3	3
122	A Solid-State Thin-Film Incandescent Light-Emitting Device. IEEE Transactions on Electron Devices, 2015, 62, 3536-3540.	1.6	3
123	High-performance organicâ€“inorganic hybrid optocouplers based on organic light-emitting diodes and a-Si:H photodiodes. Sensors and Actuators A: Physical, 2015, 236, 364-368.	2.0	3
124	Resistivity and Barrier Height of Nano-Resistors Made from Zr-Doped HfO 2 High- K Dielectric on Si Wafer. ECS Transactions, 2017, 77, 63-68.	0.3	3
125	Non-LCD Applications of a-Si:H TFTs. , 2004, , 485-505.		3
126	Two-level differential burn-in policy for spatially heterogeneous defect units in semiconductor manufacturing. Computers and Industrial Engineering, 2021, 162, 107768.	3.4	3

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127	Reactive Ion Etching Of A Multicomponent Glass Substrate. Proceedings of SPIE, 1988, , .	0.8	2
128	Nonvolatile Amorphous Silicon Thin Film Transistor Memories with the a-Si:H Embedded Gate Dielectric Structure. ECS Transactions, 2006, 3, 333-339.	0.3	2
129	Relaxation Behavior and Breakdown Mechanisms of Nanocrystals Embedded Zr-doped HfO2 High-k Thin Films for Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2008, 1071, 1.	0.1	2
130	Mechanism of Charge Storage in nc-RuO Embedded ZrHfO High-k Films. ECS Transactions, 2009, 16, 309-316.	0.3	2
131	Hysteresis of Transfer Characteristics of Floating-Gate a-Si:H Thin Film Transistor Nonvolatile Memories. Electrochemical and Solid-State Letters, 2010, 13, H460.	2.2	2
132	A novel low thermal budget thin-film polysilicon fabrication process for large-area, high-throughput solar cell production. , 2010, , .		2
133	Process effects of copper film over a step etched with a plasma-based process. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 021204.	0.6	2
134	Memory Functions of Nanocrystalline ITO Embedded Zirconium-Doped Hafnium Oxide High-<i>k</i>Capacitor with ITO Gate. Journal of the Electrochemical Society, 2012, 159, H595-H598.	1.3	2
135	Nonvolatile memories based on AlOx embedded ZrHfO high-k gate dielectric. Materials Research Society Symposia Proceedings, 2014, 1691, 37.	0.1	2
136	Light Emission Enhancement by Embedding Nanocrystalline Cadmium Selenide in Amorphous ZrHfO High-k Dielectric Thin Film Deposited on Silicon Wafer. ECS Journal of Solid State Science and Technology, 2016, 5, Q75-Q80.	0.9	2
137	Progress of Thin Film Transistor Technology. , 2018, , .		2
138	Memory Functions of Cadmium Sulfide Embedded Zr-Doped HfO₂High-k Dielectrics. ECS Journal of Solid State Science and Technology, 2018, 7, Q97-Q103.	0.9	2
139	Statistical Models of Overdispersed Spatial Defects for Predicting the Yield of Integrated Circuits. IEEE Transactions on Reliability, 2020, 69, 510-521.	3.5	2
140	Electromigration Study of Plasma Etched Copper Lines with Copper Oxide Capping Layers. ECS Transactions, 2020, 97, 51-60.	0.3	2
141	Geometrical Layout Effect on Light Intensity Distribution in SSI-LED. ECS Transactions, 2021, 102, 159-164.	0.3	2
142	Charge and Discharge of Floating-Gate Amorphous Silicon Thin Film Transistor Nonvolatile Memories. Journal of the Korean Physical Society, 2009, 54, 409-414.	0.3	2
143	Study of Electrothermal Characteristics and Emitted Light Characteristics of SSI-LED. ECS Journal of Solid State Science and Technology, 2020, 9, 065017.	0.9	2
144	Reactive Ion Etching Processes for Amorphous Germanium Alloys. Materials Research Society Symposia Proceedings, 1993, 316, 1041.	0.1	1

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145	<title>New microchannel device for protein separation and detection</title>. , 2001, , .		1
146	A new microchannel device for proteins separation and identification. , 0, , .		1
147	Plasma Hydrogenation â€“ A New Method of Reducing the k Value of the Low k Polyimide Film. Materials Research Society Symposia Proceedings, 2003, 766, 8161.	0.1	1
148	Fabrication and Characterization of Hydrogenated Amorphous Silicon Bipolar Thin Film Transistor (B-TFT). Materials Research Society Symposia Proceedings, 2004, 808, 287.	0.1	1
149	Influence of Ru Dopant on the Dielectric Properties of Zr-doped HfO2 High-k Thin Film. ECS Transactions, 2007, 6, 121-127.	0.3	1
150	Failure analysis of nanocrystals embedded high-k dielectrics for nonvolatile memories. , 2008, , .		1
151	Floating-Gate a-Si:H TFT Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2008, 1066, 1.	0.1	1
152	Hole-Trapping Mechanism and SILC of Dual-Layer nc-ITO Embedded ZrHfO High-k Nonvolatile Memories. ECS Transactions, 2010, 28, 269-276.	0.3	1
153	Plasma Etching of Copper Thin Film over a Dielectric Step and Electromigration Failure Mechanism. Materials Research Society Symposia Proceedings, 2012, 1428, 13.	0.1	1
154	Polycrystalline Silicon Thin Film Formed By Multiple Pulsed Rapid Thermal Annealing â€“ Intrinsic a-Si Film Thickness Effect. Materials Research Society Symposia Proceedings, 2012, 1426, 269-274.	0.1	1
155	Radial Growth Model for Conical Nanobridge in Resistive Switching Memory Devices. Materials Research Society Symposia Proceedings, 2013, 1562, 1.	0.1	1
156	Introduction to the Focus Issue on Oxide Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Y5-Y5.	0.9	1
157	P⁺ layer effects on a-Si:H solar cell performance. , 2014, , .		1
158	Post Deposition Annealing Temperature Effect on White-light Emitting of Sputter Deposited Zr-doped HfO2 Thin Film. Materials Research Society Symposia Proceedings, 2014, 1698, 65.	0.1	1
159	A solid state thin film incandescent light emitting device. , 2014, , .		1
160	Narrowing of Broad Band Light Emitted from a SSI-LED. ECS Transactions, 2017, 75, 17-22.	0.3	1
161	Light Sensing of a-Si:H p-i-n DiodeMechanism of Asymmetric Charge Carrier Transfer. , 2017, 1, 1-4.		1
162	Post Deposition Annealing Atmosphere Effect on Performance of Solid State Incandescent Light Emitting Device. ECS Journal of Solid State Science and Technology, 2018, 7, R3023-R3029.	0.9	1

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163	Plasma-Based Copper Etch Process and Reliability. ECS Transactions, 2018, 85, 165-170.	0.3	1
164	Molybdenum Capping Layer Effect on Electromigration Failure of Plasma Etched Copper Lines. ECS Transactions, 2019, 92, 39-46.	0.3	1
165	Auxiliary structure of nano-pinnacle prepared on silicon substrate: Improving the emission intensity by 9 times in SSI-LEDs. Materials Science in Semiconductor Processing, 2019, 93, 226-230.	1.9	1
166	Communicationâ€”Co-Planar Structured Nano-Resistor Devices. ECS Journal of Solid State Science and Technology, 2019, 8, Q223-Q225.	0.9	1
167	A Differential Burn-in Policy Considering Nonhomogeneous Distribution of Spatial Defects in Semiconductor Manufacturing. , 2020, , .		1
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